



ocket No.: 006217 USA/Consilium/Consilium

PATENT/OFFICIAL

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of :
: Nicholas A. WARD et al. :
: Serial No. 09/927,444 : Group Art Unit: 2125
: Filed: August 13, 2001 : Examiner: Sean P. Shechtman
For: DYNAMIC CONTROL OF WAFER PROCESSING PATHS IN SEMICONDUCTOR
MANUFACTURING PROCESSES

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Honorable Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

In accordance with the provisions of 37 C.F.R. 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the documents listed on the attached form PTO-1449. It is respectfully requested that the documents be expressly considered during the prosecution of this application, and that the documents be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

This Information Disclosure Statement is being filed concurrently with a Request for Continued Examination, before the mailing date of a first Office Action on the merits. No certification or fee is required.

This submission does not constitute a representation that a search has been made or that no better art exists and does not constitute an admission or representation that any of the listed

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documents is material or constitutes prior art. If it should be determined that any of the listed documents does not constitute prior art under the United States law, Applicants reserve the right to present to the Office the relevant facts and law regarding the appropriate status of such document.

The references listed on Sheet 1 of the attached PTO-1449 Forms were cited in a patentability investigation and/or a corresponding foreign or PCT application relating to the above-referenced application. The remaining references are from potentially related patent applications, and possibly other sources.

No fee is believed to be required; however, the Commissioner is hereby authorized to charge any additional fees that may be required for this submission, or credit any overpayment to deposit account no. 08-0219.

Respectfully submitted,

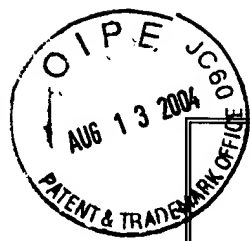
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INFORMATION DISCLOSURE
CITATION IN AN
APPLICATION
(PTO-1449)

ATTY. DOCKET NO.
006217 USA/
Consilium/Consilium

SERIAL NO.
09/927,444

APPLICANT
Nicholas A. WARD et al.

FILING DATE
August 13, 2001

GROUP
2125

U.S. PATENT DOCUMENTS

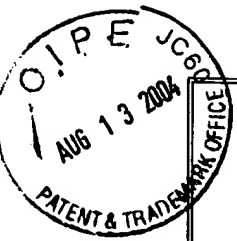
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.



INFORMATION DISCLOSURE CITATION IN AN APPLICATION (PTO-1449)				ATTY. DOCKET NO. 006217 USA/ Consilium/Consilium		SERIAL NO. 09/927,444	
				APPLICANT Nicholas A. WARD et al.			
				FILING DATE August 13, 2001		GROUP 2125	
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EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
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